Features

- AEC-Q101 Qualified
- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Halogen Free. “Green” Device (Note 1)
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

NPN Plastic Encapsulate Transistors

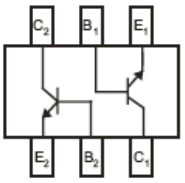
Maximum Ratings @ 25°C Unless Otherwise Specified

- Operating Junction Temperature Range: -55℃ to +150℃
- Storage Temperature Range: -55℃ to +150℃
- Thermal Resistance: 625℃/W Junction to Ambient

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	200	mA
Collector Power Dissipation (Note2)	P_C	200	mW

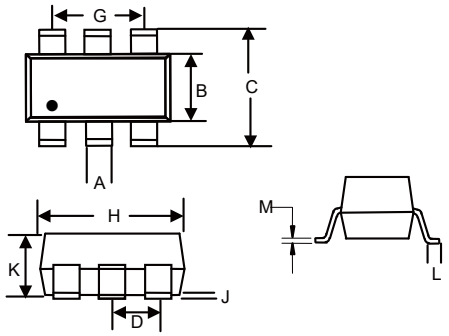
Note:
1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. Valid provided that terminals are kept at ambient temperature.

Internal Structure



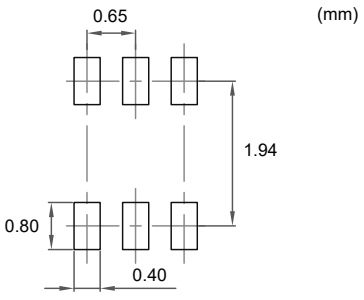
Marking: K6N

SOT-363



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.006	0.014	0.15	0.35	
B	0.045	0.053	1.15	1.35	
C	0.079	0.096	2.00	2.45	
D	0.026		0.65		TYP.
G	0.047	0.055	1.20	1.40	
H	0.071	0.087	1.80	2.20	
J	-----	0.004	-----	0.10	
K	0.031	0.043	0.80	1.10	
L	0.010	0.018	0.26	0.46	
M	0.003	0.006	0.08	0.15	

Suggested Solder Pad Layout



Electrical Characteristics @ 25°C Unless Otherwise Specified

Parameter	Symbol	Min	Typ	Max	Units	Conditions
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	60			V	I_C=10μA, I_E=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40			V	I_C=1mA, I_B=0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6			V	I_E=10μA, I_C=0
Collector-Base Cutoff Current	I_{CBO}			50	nA	V_{CB}=30V, I_E=0
Collector-Emitter Cutoff Current	I_{CEO}			50	nA	V_{CE}=30V, I_B=0
Emitter-Base Cutoff Current	I_{EBO}			50	nA	V_{EB}=5V, I_C=0
DC Current Gain(Note3)	$h_{FE(1)}$	100		300		V_{CE}=1V, I_C=10mA
	$h_{FE(2)}$	60				V_{CE}=1V, I_C=50mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.3	V	I_C=50mA, I_B=5mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	0.65		0.85	V	I_C=10mA, I_B=1mA
				0.95	V	I_C=50mA, I_B=5mA
Transition Frequency	f_T	300			MHz	V_{CE}=20V, I_C=10mA, f=100MHz
Output Capacitance	C_{obo}			4.0	pF	V_{CB}=5V, I_E=0, f=1MHz
Noise Figure	NF			5	dB	VCE=5V,Ic=0.1mA,f=1kHz,Rg=1KΩ

Note: 3.Pluse Width ≤ 300μs, Duty Cycle ≤ 2.0%

Curve Characteristics

Fig. 1 - Static Characteristics

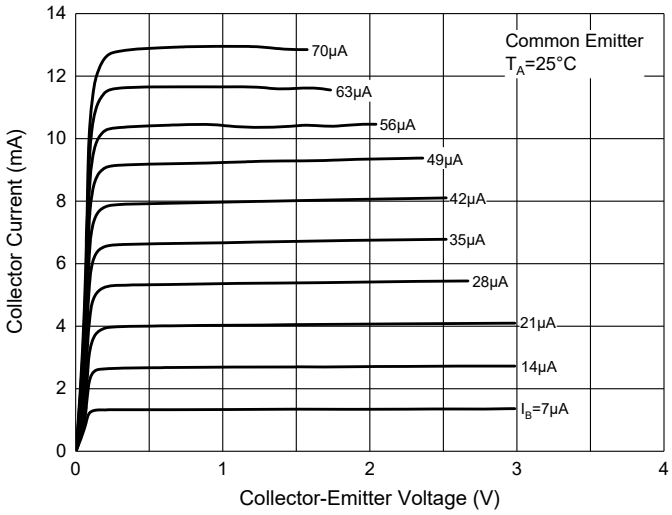


Fig. 2 - DC Current Gain Characteristics

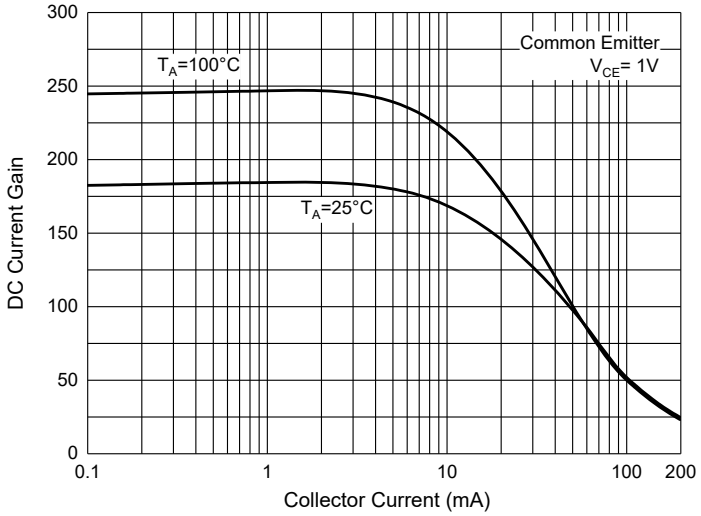


Fig. 3 - Collector-Emitter Saturation Voltage Characteristics

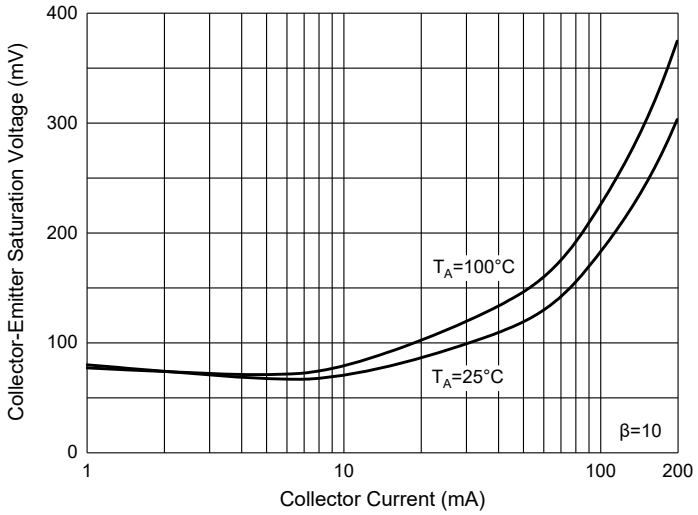


Fig. 4 - Base-Emitter Saturation Voltage Characteristics

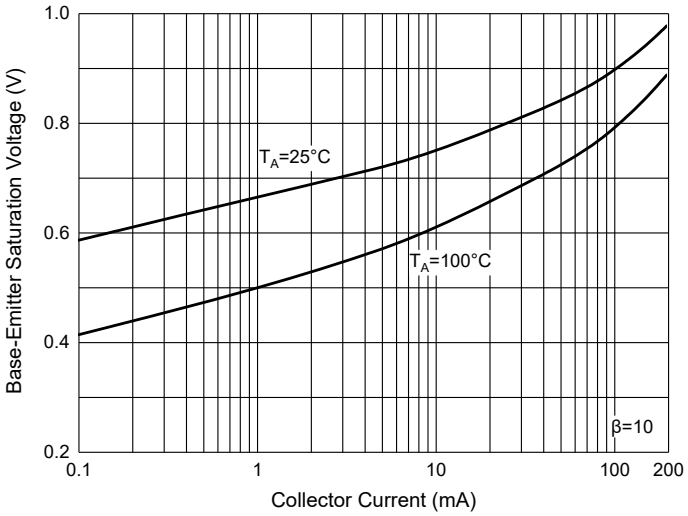


Fig. 5 - Base-Emitter Voltage Characteristics

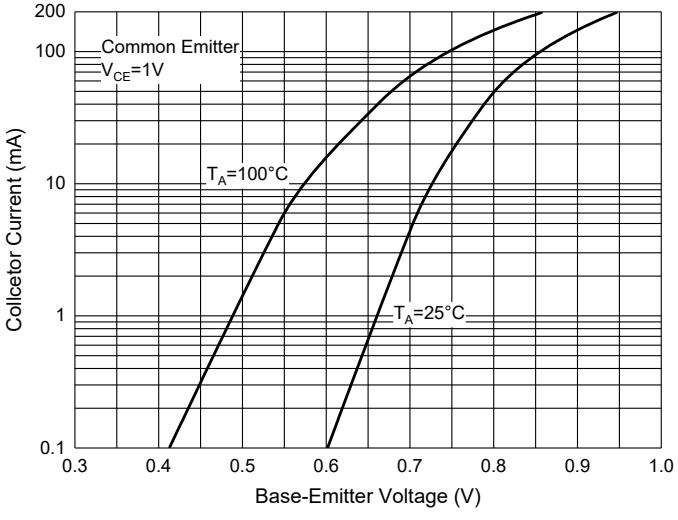
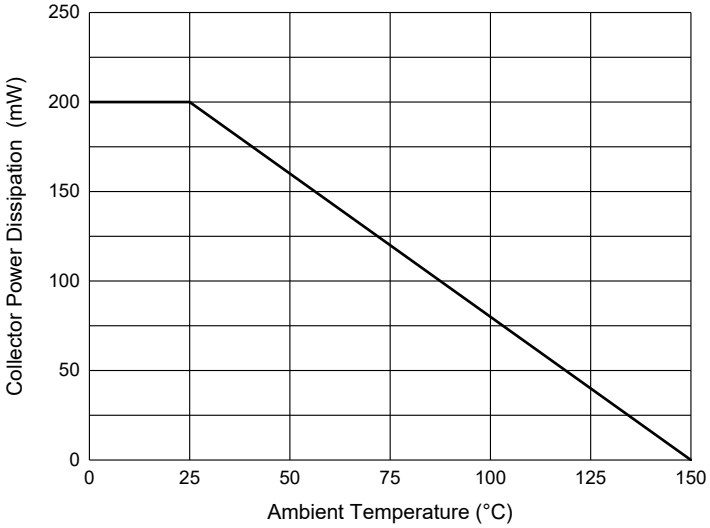


Fig. 6 - Collector Power Derating Curve



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 3Kpcs/Reel

单击下面可查看定价，库存，交付和生命周期等信息

>>MCC(美微科)